

31. A method according to claim 29, wherein the acceptor is magnesium.

32. A method according to claim 27, wherein the layers are grown as crystals by a metal organic vapor phase epitaxial growth method with nitrogen, ammonia and alkyl compound gases containing a group III element.--

REMARKS

Claims 21-32 are pending.

The title has been amended to be descriptive of the claimed invention. A reference to a related application and a priority claim have also been added.

Moreover, the specification has been amended to include corrections requested by the Examiner in the parent application. In addition, a correction has been made to Figure 2, in accordance with the Examiner's request in the parent application that all claimed features be illustrated: a layer 11 that may be present is shown by a dotted line. Since this is optional, a dotted line rather than a full line has been used. The attached Figure 2 is a redlined version showing the correction. Support for this change in Figure 2 is found on page 6, lines 16-22, of the present specification. It is believed that this correction is supported by the original disclosure and, thus, no new matter has been added. Approval by the Examiner of this correction to Figure 2 is respectfully requested.

A prompt and complete examination on the merits is earnestly solicited. If further information is required, the Examiner is invited to contact the undersigned.

Respectfully submitted,

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